

Docket No. 270968US2X PCT



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: Shinsuke HARADA, et al.

SERIAL NO: 10/531,582

GAU:

FILED: April 18, 2005

EXAMINER:

FOR: SILICON CARBIDE SEMICONDUCTOR DEVICE AND ITS MANUFACTURING METHOD

INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.97

COMMISSIONER FOR PATENTS
ALEXANDRIA, VIRGINIA 22313

SIR:

Applicant(s) wish to disclose the following information.

REFERENCES

- ☒ The applicant(s) wish to make of record the references listed on the attached form PTO-1449. Copies of the listed references are attached, where required, as are either statements of relevancy or any readily available English translations of pertinent portions of any non-English language references.
- ☐ A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

RELATED CASES

- ☐ Attached is a list of applicant's pending application(s), published application(s) or issued patent(s) which may be related to the present application. In accordance with the waiver of 37 CFR 1.98 dated September 21, 2004, copies of the cited pending applications are not provided. Cited published and/or issued patents, if any, are listed on the attached PTO form 1449.
- ☐ A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

CERTIFICATION

- ☐ Each item of information contained in this information disclosure statement was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.
- ☐ No item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, having made reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this statement.

DEPOSIT ACCOUNT

- ☒ Please charge any additional fees for the papers being filed herewith and for which no check or credit card payment is enclosed herewith, or credit any overpayment to deposit account number 15-0030. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

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Form PTO 1449
(Modified)U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICEATTY DOCKET NO.
270968US2X PCTSERIAL NO.
10/531,582

LIST OF REFERENCES CITED BY APPLICANT

APPLICANT
Shinsuke HARADA, et al.FILING DATE
April 18, 2005

GROUP

U.S. PATENT DOCUMENTS

| EXAMINER INITIAL | | DOCUMENT NUMBER | DATE | NAME | CLASS | SUB CLASS | FILING DATE IF APPROPRIATE |
|---------------------|----|--------------------|------|------|-------|--------------|-------------------------------|
| | AA | | | | | | |
| | AB | | | | | | |
| | AC | | | | | | |
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FOREIGN PATENT DOCUMENTS

| | | DOCUMENT NUMBER | DATE | COUNTRY | TRANSLATION | |
|--|----|--------------------|----------|----------------------------|-------------|----|
| | | | | | YES | NO |
| | AO | 2001-119025 | 04/27/01 | JP (with English abstract) | | NO |
| | AP | 2000-150875 | 05/30/00 | JP (with English abstract) | | NO |
| | AQ | 1-144683 | 06/06/89 | JP (with English abstract) | | NO |
| | AR | 61-013667 | 01/21/86 | JP (English abstract only) | | NO |
| | AS | | | | | |
| | AT | | | | | |
| | AU | | | | | |
| | AV | | | | | |

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)

| | | | | | | |
|--|----|--|--|--|--|--|
| | AW | CAPANO, M.A. et al. "Ionization energies and electron mobilities in phosphorus- and nitrogen- implanted 4H-silicon carbide", Journal of Applied Physics, vol. 87, no. 12, pages 8773-8777 2000 | | | | |
| | AX | HARADA, Shinsuke et al. "High Channel Mobility in Normally-Off 4H-SiC Buried Channel MOSFETs", IEEE Electron Device Letters, vol. 22, no. 6, pages 272-274 2001 | | | | |
| | AY | | | | | |
| | AZ | | | | | <input type="checkbox"/> Additional References sheet(s) attached |

Examiner

Date Considered

*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

U.S. PCT Application Serial No.: 10/531,582
Docket No.: 270968US2X PCT

STATEMENT OF RELEVANCY

- 1) References AO-AR have been cited in the International Search Report. Copies of these references are being submitted herewith only when not automatically provided by the International Searching Authority.
- 2) References _____ have been cited in the corresponding _____ Search Report. A copy of these references is being submitted herewith.
- 3) References AW, AX are discussed in the specification. A copy of these references is being submitted here with.
- 4) References _____ are additional prior art known to Applicant. A copy of these references is being submitted herewith.